DISCRETE SEMICONDUCTORS

DATA SHEET

PEMB11; PUMB11 PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

Product specification Supersedes data of 2001 Sep 13 2003 Oct 03





 $\mathsf{k}\Omega$

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

PEMB11; PUMB11

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	-50	V
I _O	output current (DC)	_	-100	mA
TR1	PNP	_	_	_
TR2	PNP	_	_	-
R1	bias resistor	10	_	kΩ

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QUICK REFERENCE DATA

bias resistor

DESCRIPTION

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACE	(AGE	MARKING CODE(1)	NPN/PNP	NPN/NPN
I TPE NOWIBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMB11	SOT666	_	B1	PEMD3	PEMH11
PUMB11	SOT363	SC-88	B*1	PUMD3	PUMH11

R2

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING
I TPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION
PEMB11	6 5 4	1	emitter TR1
PUMB11	6 5 4	2	base TR1
	R1 R2	3	collector TR2
	TR2	4	emitter TR2
	TR1	5	base TR2
	$\left[\begin{array}{c c} & R2 \\ \hline \end{array}\right]$ R2 R1	6	collector TR1
	1 2 3 Top view MAM477		
	I OP VICTY INJUSTEE!		

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ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
TIPE NUMBER	NAME	DESCRIPTION	VERSION
PEMB11	_	plastic surface mounted package; 6 leads	SOT666
PUMB11	_	plastic surface mounted package; 6 leads	SOT363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT			
Per transistor								
V _{CBO}	collector-base voltage	open emitter	_	-50	V			
V _{CEO}	collector-emitter voltage	open base	_	-50	V			
V _{EBO}	emitter-base voltage	open collector	_	-10	V			
VI	input voltage							
	positive		_	+10	V			
	negative		_	-40	V			
Io	output current (DC)		_	-100	mA			
I _{CM}	peak collector current		_	-100	mA			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C						
	SOT363	note 1	_	200	mW			
	SOT666	notes 1 and 2	_	200	mW			
T _{stg}	storage temperature		-65	+150	°C			
Tj	junction temperature		_	150	°C			
T _{amb}	operating ambient temperature		-65	+150	°C			
Per device		•		,				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C						
	SOT363	note 1	-	300	mW			
	SOT666	notes 1 and 2	_	300	mW			

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0$	_	_	-400	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	30	_	_	
V _{CEsat}	saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-1.1	-0.8	V
$V_{i(on)}$	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -10 \text{ mA}$	-2.5	-1.8	_	V
R1	input resistor		7	10	13	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

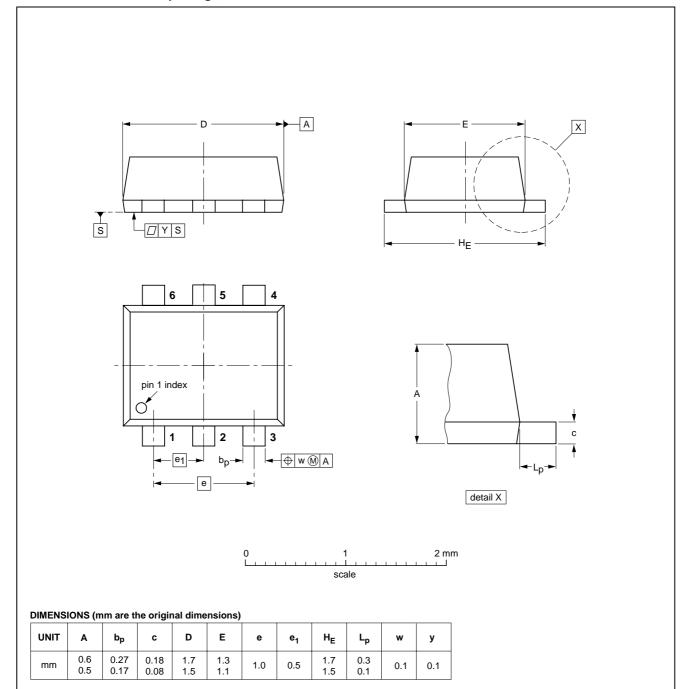
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PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



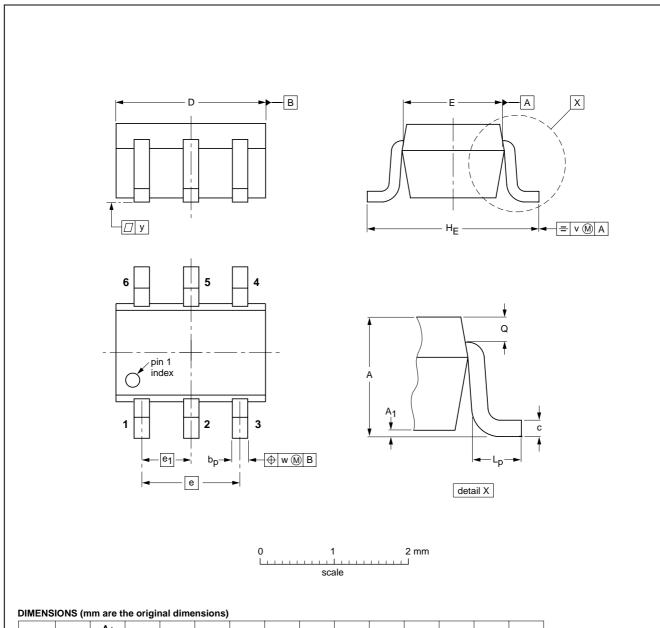
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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Plastic surface mounted package; 6 leads

SOT363



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE	REFERENCES EUROPEAN 16					
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
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Notes

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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